



## POWER DISCRETES & MODULES

- ▶ Silicon Carbide (SiC)
- ▶ BJT (BiPolar Junction Transistor)
  - BJT Modules (Power Integrated Circuit, PIC)
  - Darlingtons Transistors
  - Darlingtons Transistor Array
  - NPN PNP Complimentary Transistor
  - **NPN Transistor**
  - PNP Transistor
- ▶ Current Regulator Diodes
- ▶ Diodes
- ▶ FRED 50-1700V
- ▶ IGBT
- ▶ JFET
- ▶ MOSFET
- ▶ Power Modules
- ▶ RF/Microwave Power Transistor Products
- ▶ Silicon Rectifiers
- ▶ Solar Array Diode
- ▶ Transient Voltage Suppressors (TVS)
- ▶ Zener Diodes
- ▶ Legacy Power Discrettes & Modules

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# 2N657

**Product Status**

■ In Production

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Electrical Rating	Symbol	Min	Typ	Max	Unit
DC Current Gain	HFE	30		90	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector Current (dc)	$I_C$			0.2	A
Collector-Emmitter Voltage (Base Open)	$V_{CEO}$			100	V
Junction Temperature (°C)	$T_J$			200	°C

This part can be found in the following product categories:

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